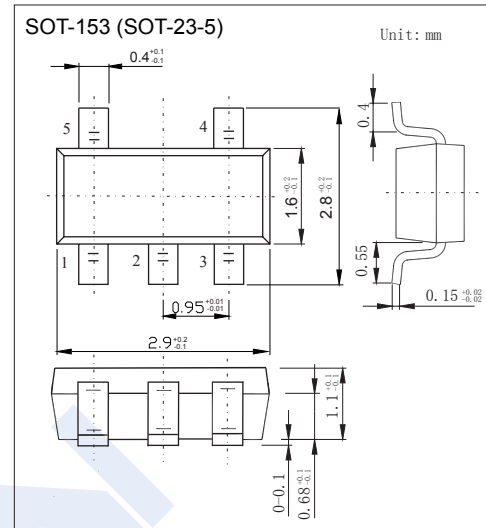
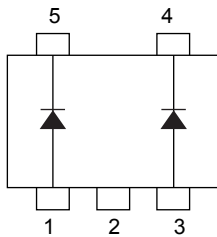


Schottky Diodes

SBE807 (KBE807)

■ Features

- Low switching noise.
- Low reverse current
- High frequency rectification

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|--|---------------|------------|---------------------------|
| Repetitive Peak Reverse Voltage | VRRM | 30 | V |
| Nonrepetitive Peak Reverse Surge Voltage | VRSM | 35 | |
| Average Output Current | I_o | 1 | A |
| Surge Forward Current @ 50Hz | IFSM | 10 | |
| Thermal Resistance Junction to Ambient | R θ JA | 111 | $^\circ\text{C}/\text{W}$ |
| Junction Temperature | TJ | 125 | $^\circ\text{C}$ |
| Storage Temperature range | Tstg | -55 to 125 | |

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---------------------------------|--------|--|-----|-----|------|---------------|
| Reverse breakdown voltage | VR | IR= 0.2mA | 30 | | | V |
| Forward voltage | VF | IF= 0.7 A | | | 0.5 | |
| | | IF= 1 A | | | 0.53 | |
| Reverse voltage leakage current | IR | VR= 16 V | | | 15 | μA |
| Junction capacitance | Cj | VR= 10 V, f= 1 MHz | | 27 | | pF |
| Reverse recovery time | trr | IF=IR=100mA, Irr=0.1xIR, RL=100 Ω | | | 10 | ns |

■ Marking

| Marking | SJ |
|---------|----|
| | |

Schottky Diodes

SBE807 (KBE807)

Typical Characteristics

